## nexperia

## **Quarterly Reliability Monitoring Results**

Quarters: Q1/2021 to Q4/2021

Based on structural similarity

Supplier		User Part Number						
Nexperia B.V. Name of Laboratory Assembly reliability labs Based on AEC-Q101 Test		BCX54 Part Description						
								Nexperia DHAM Small Signal Bipolar Transistor
		SMD package						
		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
			TEST					
	Pre- and Post-Stress							
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113						
		Bake Tamb = 125 °C	24 hours					
	PC	Soak Tamb = 85 °C, RH = 85%	168 hours					
# A1	Preconditioning	Reflow soldering	3 cycles	849	61170	0		
		MIL-STD-750-1						
	HTRB	M1039 Method A						
	5	Tj = Tjmax, Vr = 100% of max. datasheet						
# B1	Bias	reverse voltage	1000 hours	202	16160	0		
	тс	150000 4104						
	Temperature Cycling	JESD22-A104 -65 °C to Tjmax, not to exceed 150°C	1000		12600	0		
# A4	Temperature Cycling		1000 cycles	171	13680	0		
	AC	JESD22-A102 Tamb = 121 °C, RH = 100 %						
# AD - H	Autoclave	Pressure = 205 kPa (29.7 psia)		170	12040	0		
# A3 alt	Autoclave	riessure – 203 kra (23.7 psia)	96 hours	173	13840	0		
	H3TRB	JESD22-A101						
	High Humidity High	Tamb = $85 ^{\circ}$ C, RH = $85\%$ , VR = $80\%$ of						
# A2 alt	Temperature Reverse Bias		1000 hours	173	13840	0		
# AZ dil			1000 110015	175	13640	0		
	IOL	MIL-STD-750 Method 1037 ton = toff, devices powered to insure $\Delta T_j$ =						
# A5	Intermittent Operating Life		1000 hours	197	15760	0		
# A5	Internitient Operating Life	100 C 101 15000 Cycles	1000 Hours	191	13/00	U		
	RSH	JESD22-A111						
# C8	Resistance to Solder Heat		10 s	135	4050	0		
# 0	SD	200 0 - 0 0	10.5	100	4000	U		
# C10	Solderability	J-STD-002		342	3420	0		
+ CI0	Solderability	3 510 002		342	3420	U		

[1] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

## **Calculation of FIT and MTTF**

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia DHAM	Small Signal Bipolar Transistor	16160	0	0.26	3.81E+09

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